

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1-16. (Canceled)

17. (Currently amended): A semiconductor device as claimed in claim 16 A semiconductor device having a semiconductor chip,

first electrodes formed on said semiconductor chip,

barrier metals formed on said first electrodes and having laminated structures, and

a plurality of second protruded electrodes, which serve as external connection terminals,

formed on said barrier metals, wherein said barrier metals comprising:

a lowermost conductive metal layer laminated on said first electrodes, said lowermost conductive metal layer being made of a metal selected from the group consisting of titanium (Ti), chromium (Cr) and molybdenum (Mo) and having a joining property with said first electrodes;

an intermediate conductive metal layer laminated on said lowermost conductive metal layer, said intermediate conductive metal layer being made of nickel (Ni); and

an uppermost conductive metal layer laminated on said one or more intermediate conductive metal layer, said uppermost conductive metal layer being made of a material which easily alloys with the nickel of said intermediate conductive metal layer and which has resistance to oxidation, said uppermost conductive metal layer being made of a metal selected from the group consisting of platinum (Pt), palladium (Pd), silver (Ag) and rhodium (Rh) or of an alloy containing

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a metal selected from the group consisting of gold (Au), platinum (Pt), palladium (Pd), silver (Ag) and rhodium (Rh),

wherein ~~the a~~ weight of said uppermost conductive metal layer is less than 2 weight % of  
~~the a weight of the bump to be second protruded electrode formed thereon.~~